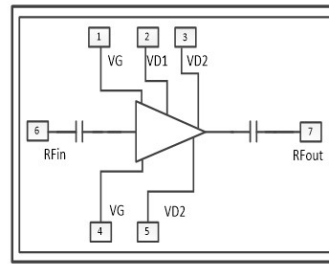


Performance

- Frequency: 2~8GHz
- Typical Signal Gain: 25dB
- Typical Pout: 44dBm @28V
- Typical PAE: 32%
- Bias: 28V, -1.8V (Typ.)
- Size: 3.5*4.6mm*0.08mm
- Technology: 0.25um HEMT

Function Diagram

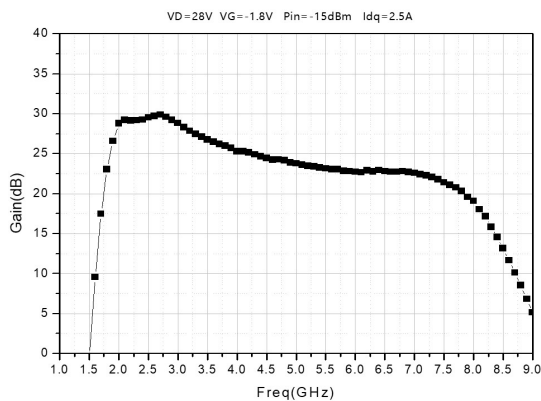


Electrical Specifications ($V_d=28V$, $I_{dq}=2.5A$, F: 2~8GHz, CW)

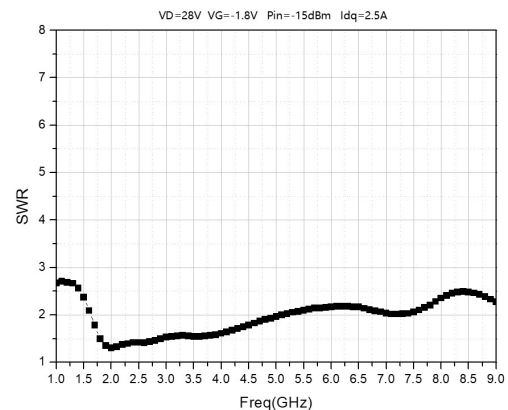
Parameter	Min	Typical	Max	Unit
Small Signal Gain	-	25	-	dB
Power Gain	-	16	-	dB
Saturated Power	-	44	-	dBm
Power Added Efficiency	-	32	-	%

Test Curves ($V_d=28V$, $V_g=-1.8V$, F: 6-18GHz, CW)

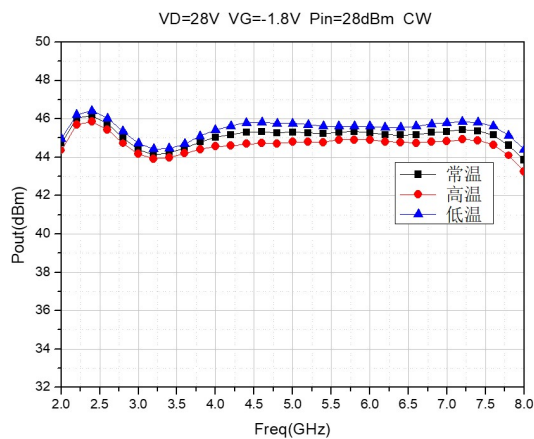
Small Signal Gain vs. Freq



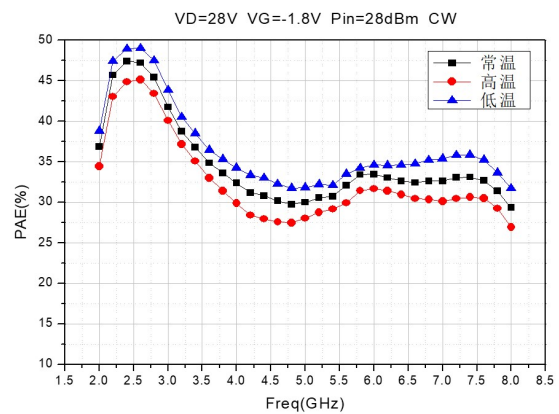
Input VSWR vs. Freq



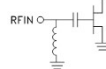
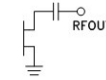
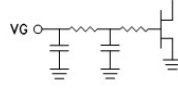

Output Power vs. Freq



PAE vs. Freq



Pads Definition

No	Description	Equivalent Circuits
RFin	RF signal Input port, connect to 50 ohm system, extra block capacitor is needed.	
RFout	RF signal Output port, connect to 50 ohm system, no block capacitor is needed.	
VG	Amplifier gate bias, external 330pF, 1000pF capacitor is needed.	
VD	Amplifier drain bias, external 330pF, 1000pF capacitor is needed.	
GND	Bottom must be well grounded	